

BTA12-600BW3G, BTA12-800BW3G





Description

Designed for high performance full—wave ac control applications where high noise immunity and high commutating di/dt are required.

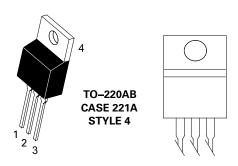
Features

- Blocking Voltage to 800 V
- On-State Current Rating of 12 A RMS at 25°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dV/dt

 2000 V/µs minimum at
 125°C
- Minimizes Snubber
 Networks for Protection

- Industry Standard TO-220AB Package
- High Commutating dl/ dt – 2.5 A/ms minimum at 125°C
- Internally Isolated (2500 VRMS)
- These Devices are Pb-Free and are RoHS Compliant

Pin Out



Functional Diagram



Additional Information







Samples



Maximum Ratings (T₁ = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_J = -40^{\circ}$ to 125°C)	BTA12-600BW3G BTA12-800BW3G	V _{DRM} , V _{RRM}	600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_{\rm C} = 80^{\circ}{\rm C}$)		I _{T (RMS)}	12	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _C = 25°C)		I _{TSM}	105	А
Circuit Fusing Consideration (t = 8.3 ms)		l ² t	46	A²sec
Non-Repetitive Surge Peak Off-State Voltage ($T_J = 25^{\circ}\text{C}$, t = 10ms)		V _{DSM} /V _{RSM}	V _{DSM} /V _{RSM} +100	V
Peak Gate Current ($T_J = 125$ °C, $t = 20$ ms)		I _{GM}	4.0	А
Peak Gate Power (Pulse Width ≤ 1.0 µs, T _C = 80°C)		P _{G(AV)}	20	W
Average Gate Power ($T_J = 125^{\circ}\text{C}$)		P _{G(AV)}	1.0	W
Operating Junction Temperature Range		T _J	-40 to +125	°C
Storage Temperature Range		T _{stg}	-40 to +125	°C
RMS Isolation Voltage (t = 300 ms, R.H. \leq 30%, T_A = 25°C)		V _{iso}	2500	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Thermal Characteristics

	Rating	Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R _{suc} R _{sua}	2.5 60	°C/W
Maximum Lead Temperature for Sold 10 seconds	T _L	260	°C	

Electrical Characteristics • **OFF** (T₁ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T, = 25°C	I _{DRM} ,	-	-	0.005	A
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	T _J = 125°C	I _{RRM}	-	-	2.0	mA mA

Electrical Characteristics - ON $(T_1 = 25^{\circ}\text{C unless otherwise noted}; \text{ Electricals apply in both directions})$

Characteristic		Symbol	Min	Тур	Max	Unit
Forward On-State Voltage (Note 2) ($I_{TM} = \pm 17 \text{ A Peak}$)		V_{TM}	-	-	1.55	V
	MT2(+), G(+)		2.0	-	50	mA
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}, R_L = 30 \Omega$)	MT2(+), G(-)	I _{GT}	2.0	_	50	
	MT2(-), G(-)		2.0	-	50	
Holding Current $(V_D = 12 \text{ V}, \text{ Gate Open, Initiating Current} = \pm 100 \text{ mA})$		I _H	_	_	50	mA
	MT2(+), G(+)		-	-	70	mA
Latching Current ($V_D = 24 \text{ V}$, $I_G = 42 \text{ mA}$)	MT2(+), G(-)	I	_	_	80	
	MT2(-), G(-)		_	-	70	
	MT2(+), G(+)	V _{GT}	0.5	_	1.7	V
Gate Trigger Voltage ($V_D = 12 \text{ V}, R_L = 30 \Omega$)	MT2(+), G(-)		0.5	_	1.1	
	MT2(-), G(-)		0.5	-	1.1	
	MT2(+), G(+)	V _{GD}	0.2	_	-	
Gate Non-Trigger Voltage (T ₁ = 125°C)	MT2(+), G(-)		0.2	-	-	V
	MT2(-), G(-)		0.2	-	_	

^{2.} Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

^{1.} V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



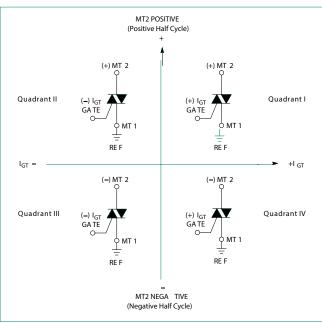
Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current, See Figure 10. (Gate Open, $T_J = 125$ °C, No Snubber)	(dl/dt)c	2.5	_	_	A/ms
Critical Rate of Rise of On–State Current ($T_J = 125$ °C, $f = 120$ Hz, $I_G = 2 \times I_{GT}$, $tr \le 100$ ns)	dl/dt	-	_	50	A/µs
Critical Rate of Rise of Off-State Voltage $(V_D = 0.66 \times V_{DRM'})$ Exponential Waveform, Gate Open, $T_J = 125$ °C)		2000	_	_	V/µs

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
IRRM	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current

Quadrant Definitions for a Triac



All polarities are referenced to MT1.
With in–phase signals (using standard AC lines) quadrants I and III are used

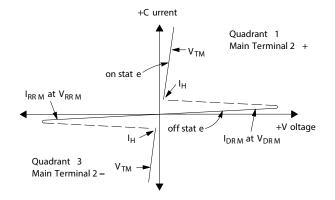
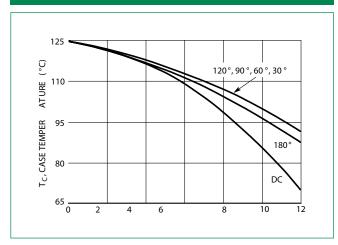




Figure 1. RMS Current Derating



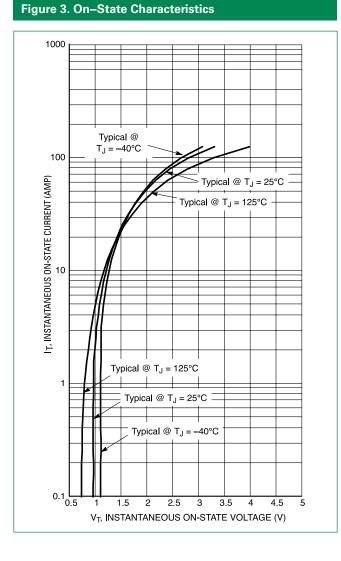


Figure 2. On-State Power Dissipation

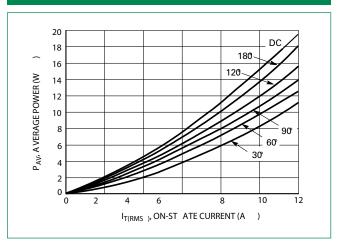


Figure 4. Thermal Response

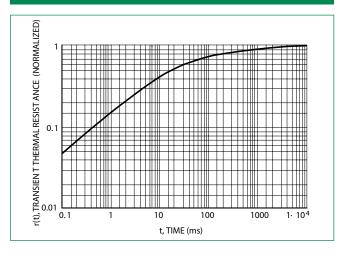


Figure 5. Hold Current Variation

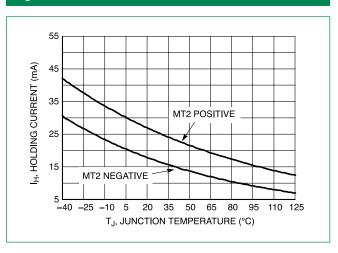




Figure 6. Gate Trigger Current Variation

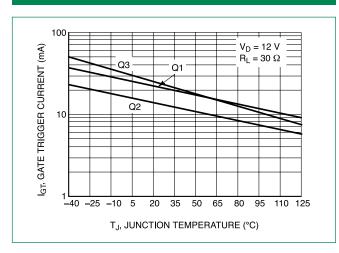


Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential Waveform)

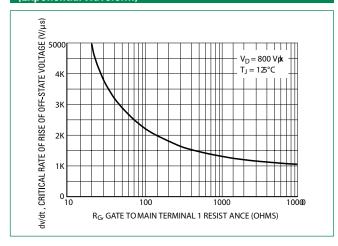


Figure 7. Gate Trigger Voltage Variation

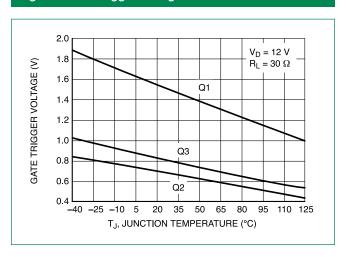


Figure 10. Latching Current Variation

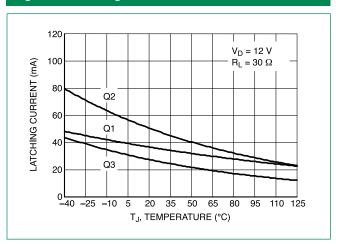
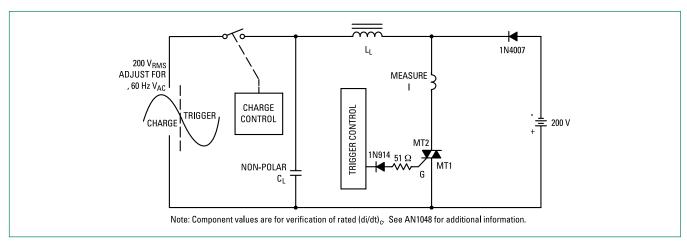


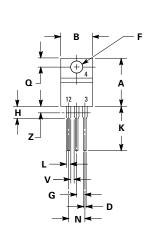
Figure 9. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)

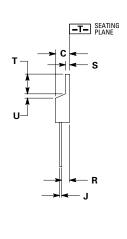


Note: Component values are for verification of rated (di/dt)c. See AN1048 for additional information

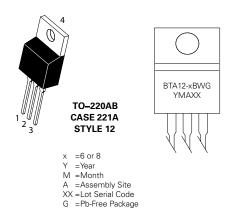


Dimensions





Part Marking System



5.	Inches		Millin	neters	
Dim	Min	Max	Min	Max	
Α	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
Н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
K	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
N	0.195	0.205	4.95	5.21	
Q	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
s	0.045	0.060	1.14	1.52	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z	_	0.080		2.04	

Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	No Connection		

Ordering Information

Device	Package	Shipping
BTA12-600BW3G	TO-220AB (Pb-Free)	500 Units / Box
BTA12-800BW3G	TO-220AB (Pb-Free)	500 Units / Box

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

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